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(54) Title: PROCESS FOR CHEMICAL-MECHANICAL POLISHING OF METAL SUBSTRATES

(57) Abstract: Abrasive composition for the chemical-mechanical polishing in one stage of substrates used in the microelectronics semiconductors industry containing at least one metal layer and one insulator layer, comprising an acid aqueous suspension of individualized particles of colloidal silica, not linked to each other by siloxane bonds, having a mean particle diameter of between 5 and 20 nm and an oxidizing agent, and chemical-mechanical polishing process using such a composition.